N-Channel Silicon MOSFET



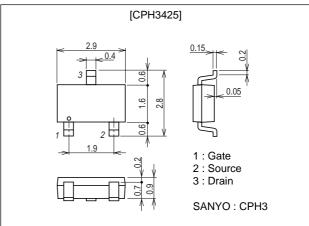
## Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

## **Package Dimensions**

unit : mm

2152A



# **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		100	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	۱D		0.5	A
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	2	A
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm <sup>2</sup> X0.8mm)	0.9	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

### Electrical Characteristics at Ta=25°C

Symbol	Conditions	Ratings			Unit
		min	typ	max	Unit
V(BR)DSS	ID=1mA, VGS=0	100			V
IDSS	VDS=100V, VGS=0			1	μA
IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0			±10	μA
VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =250mA	0.4	0.8		S
R <sub>DS</sub> (on)1	ID=250mA, VGS=10V		1.4	1.85	Ω
R <sub>DS</sub> (on)2	ID=250mA, VGS=4V		1.8	2.5	Ω
	V(BR)DSS IDSS IGSS VGS(off)  yfs  RDS(on)1	V(BR)DSS ID=1mA, VGS=0   IDSS VDS=100V, VGS=0   IGSS VGS=±16V, VDS=0   VGS(off) VDS=10V, ID=1mA    yfs  VDS=10V, ID=250mA   RDS(on)1 ID=250mA, VGS=10V	V(BR)DSS ID=1mA, VGS=0 100   IDSS VDS=100V, VGS=0 100   IGSS VGS=±16V, VDS=0 100   VGS(off) VDS=10V, ID=1mA 1.2    yfs  VDS=10V, ID=250mA 0.4   RDS(on)1 ID=250mA, VGS=10V 100	Symbol Conditions min typ   V(BR)DSS ID=1mA, VGS=0 100 100   IDSS VDS=100V, VGS=0 100 100   IGSS VGS=±16V, VDS=0 100 100   VGS(off) VDS=10V, ID=1mA 1.2 100   Iyfs VDS=10V, ID=250mA 0.4 0.8   RDS(on)1 ID=250mA, VGS=10V 1.4 1.4	Symbol Conditions min typ max   V(BR)DSS ID=1mA, VGS=0 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 </td

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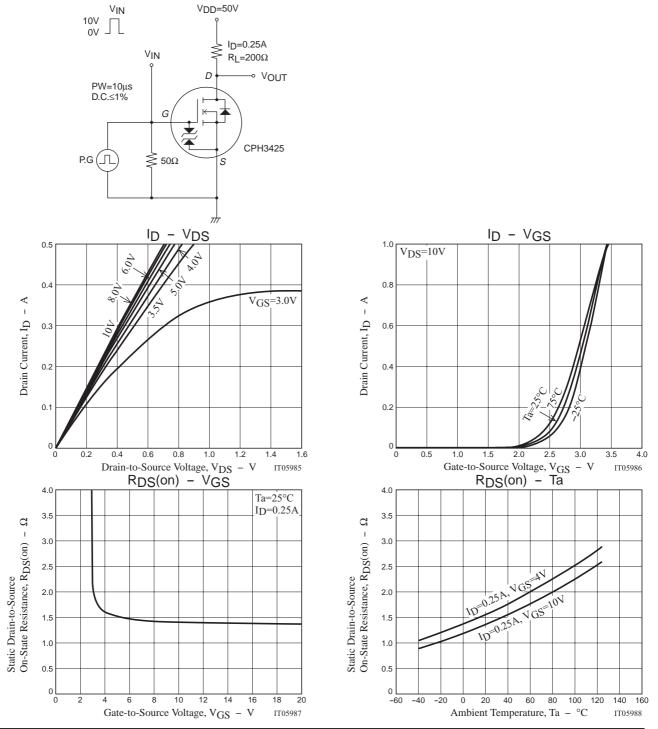
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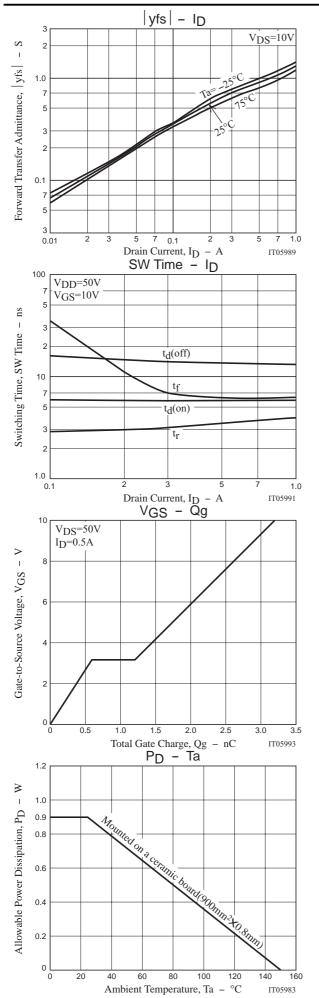
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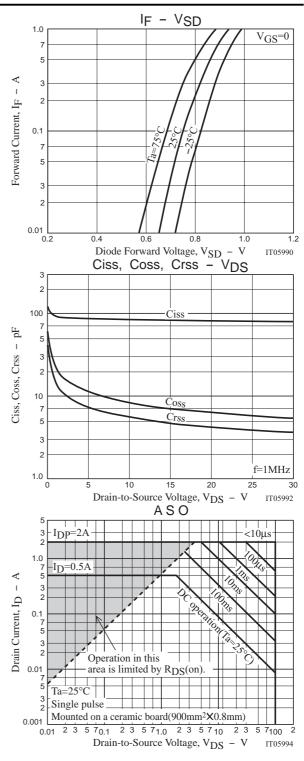
SANYO Electric Co., Ltd. Semiconductor Company TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN Continued from preceding page.

Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Input Capacitance	Ciss	V <sub>DS</sub> =20V, f=1MHz		80		pF
Output Capacitance	Coss	V <sub>DS</sub> =20V, f=1MHz		6.5		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =20V, f=1MHz		4		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		6		ns
Rise Time	tr	See specified Test Circuit.		3		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		14		ns
Fall Time	tf	See specified Test Circuit.		8		ns
Total Gate Charge	Qg	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =0.5A		3.2		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =0.5A		0.6		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =0.5A		0.6		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =0.5A, V <sub>GS</sub> =0		0.87	1.2	V

## Switching Time Test Circuit







Note on usage : Since the CPH3425 is designed for high-speed switching applications, please avoid using this device in the vicinity of highly charged objects.

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